Appl. No.

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acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and

(b) organic bridged silane of the formula R<sup>3</sup><sub>p</sub>Y<sub>3-p</sub>Si-M-SiR<sub>4q</sub>Z<sub>3-q</sub> (where each of R<sup>1</sup> and R<sup>4</sup> which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si), wherein the organic bridged silane is synthesized by reacting a silane monomer containing a Si-H with a silane monomer containing aliphatic unsaturated carbon (-CH=CH<sub>2</sub>) in the presence of a catalyst.

7. (Amended) A process for preparing an organic silicate polymer having a flexible bridge unit in the network comprising the step of:

reacting the following component (a) with the following component (b) in an organic solvent after addition of water and catalyst:

- (a) organosilane of the formula  $R^1{}_mR^2{}_n\mathrm{SiX}_{4\text{-m-n}}$  (where each of  $R^1$  and  $R^2$  which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl or aryl group; X is a hydrolysable group selected from halide, alkoxy or acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and
- (b) organic bridged silane of the formula  $R^3_p Y_{3-p} Si-M-SiR_{4q} Z_{3-q}$  (where each of  $R^1$  and  $R^4$  which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si),

wherein the organic silicate polymer has a weight average molecular weight within a range of from 500 to 100,000.

8. (Amended) An interlayer dielectric film for a semiconductor device comprising an organic silicate polymer having a flexible bridge unit in the network prepared by crosslinking reaction between the following components (a) and (b):



Appl. No.

09/776,383

02/02/2001 Filed

- organosilane of the formula R1mR2nSiX4-m-n (where each of R1 and R2 which may (a) be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorinecontaining alkyl or aryl group; X is a hydrolysable group selected from halide, alkoxy or acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and
- organic bridged silane of the formula  $R^3_p Y_{3-p} Si-M-SiR_{4q} Z_{3-q}$  (where each of  $R^1$ and R4 which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si).
- A semiconductor device comprising an interlayer dielectric film (Amended) 9. comprising an organic silicate polymer having a flexible bridge unit in the network prepared by crosslinking reaction between the following components (a) and (b):
- organosilane of the formula  $R^1_m R^2_n SiX_{4-m-n}$  (where each of  $R^1$  and  $R^2$  which may (a) be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorinecontaining alkyl or aryl group; X is a hydrolysable group selected from halide, alkoxy or acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and
- organic bridged silane of the formula R<sup>3</sup><sub>p</sub>Y<sub>3-p</sub>Si-M-SiR<sub>4q</sub>Z<sub>3-q</sub> (where each of R<sup>1</sup> and R4 which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si).
- A process for preparing an interlayer dielectric film for a (Amended) 10. semiconductor device comprising the steps of:
- dissolving an organic silicate polymer in a solvent to obtain a solution, the organic a) silicate polymer having a flexible bridge unit in the network prepared by crosslinking reaction between the following components (i) and (ii):

Appl. No.

09/776,383 02/02/2001

Filed

- organosilane of the formula  $R^1{}_mR^2{}_nSiX_{4\text{-m-n}}$  (where each of  $R^1$  and  $R^2$ (i) which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl or aryl group; X is a hydrolysable group selected from halide, alkoxy or acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and
- organic bridged silane of the formula  $R^3_{\ p} Y_{3-p} Si-M-Si R_{4q} Z_{3-q}$  (where each (ii) of R1 and R4 which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si);
  - spin coating the solution obtained in step a) on a substrate to form a film; b)
  - drying the film obtained in step b) to obtain a dried film; and c)
- curing the dried film obtained in step c) at a temperature of 300 to 500 °C, d) whereby an interlayer dielectric film is obtained.
- A process for preparing a semiconductor device comprising an (Amended) / 11. interlayer dielectric film, the process comprising the steps of:
- dissolving an organic silicate polymer in a solvent to obtain a solution, the organic a) silicate polymer having a flexible bridge unit in the network prepared by crosslinking reaction between the following components (i) and (ii):
- organosilane of the formula  $R^1{}_mR^2{}_nSiX_{4\text{-m-n}}$  (where each of  $R^1$  and  $R^2$ (i) which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl or aryl group; X is a hydrolysable group selected from halide, alkoxy or acyloxy; and m and n are integers of from 0 to 3 satisfying  $0 \le m+n \le 3$ ) or a partially hydrolyzed condensate thereof; and
- organic bridged silane of the formula  $R^3_{\ p} Y_{3\text{-}p} Si\text{-}M\text{-}SiR_{4q} Z_{3\text{-}q}$  (where each (ii) of R1 and R4 which may be the same or different, is a non-hydrolysable group selected from hydrogen, alkyl, fluorine-containing alkyl, alkenyl or aryl; each of Y and Z which may be the same or different, is a hydrolysable group selected from halide, alkoxy or acyloxy; M is alkylene or arylene group; and p and q are integers of from 0 to 2) or a cyclic oligomer with organic bridge unit (Si-M-Si);

Appl. No. Filed 09/776,383 02/02/2001

b) spin coating the solution obtained in step a) on a substrate to form a film;

c) drying the film obtained in step b) to obtain a dried film; and

d) curing the dried film obtained in step c) at a temperature of 300 to 500 °C,

whereby an interlayer dielectric film is obtained.